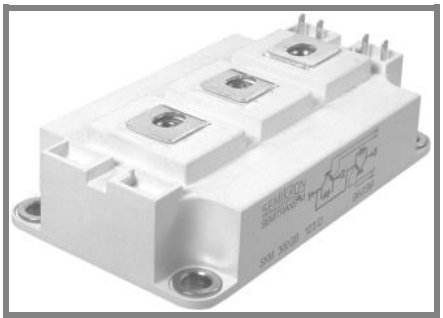
SKM 200GB173D



SEMITRANS® 3

IGBT Modules

SKM 200GB173D

SKM 200GB173D1

SKM 200GAL173D

SKM 200GAR173D

Features

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- N channel , Homogeneous Si
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- DC bus voltage 750 - 1200 V_{DC}
- Public transport (auxiliary syst.)
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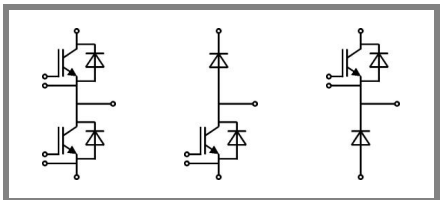
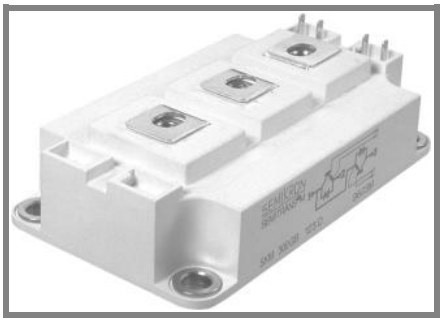


GB **GAL** **GAR**

Absolute Maximum Ratings	T_c = 25 °C, unless otherwise specified			
Symbol	**Conditions**		**Values**	**Units**
IGBT				
V_{CES}	T_j = 25 °C		1700	V
I_C	T_j = 150 °C	T_{case} = 25 °C	220	A
		T_{case} = 80 °C	150	A
I_{CRM}	I_{CRM}=2xI_{Cnom}		300	A
V_{GES}			± 20	V
t_{psc}	V_{CC} = 1200 V; $V_{GE} \leq$ 20 V; V_{CES} < 1700 V	T_j = 125 °C	10	µs
Inverse Diode				
I_F	T_j = 150 °C	T_{case} = 25 °C	150	A
		T_{case} = 80 °C	100	A
I_{FRM}	I_{FRM}=2xI_{Fnom}		300	A
I_{FSM}	t_p = 10 ms; sin.	T_j = 150 °C	1450	A
Freewheeling Diode				
I_F	T_j = 150 °C	T_{case} = 25 °C	230	A
		T_{case} = 80 °C	150	A
I_{FRM}	I_{FRM}=2xI_{Fnom}		400	A
I_{FSM}	t_p = 10 ms; sin	T_j = 150 °C	2200	A
Module				
$I_{t(RMS)}$			500	A
T_{vj}			- 40 ... + 150	°C
T_{stg}			- 40 ... + 125	°C
V_{isol}	AC, 1 min.		4000	V

Characteristics	T_c = 25 °C, unless otherwise specified					
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Units**
IGBT						
$V_{GE(th)}$	V_{GE} = V_{CE}, I_C = 10 mA		4,8	5,5	6,2	V
I_{CES}	V_{GE} = 0 V, V_{CE} = V_{CES}	T_j = 25 °C		0,1	0,3	mA
V_{CE0}		T_j = 25 °C		1,65	1,9	V
		T_j = 125 °C		1,9	2,15	V
r_{CE}	V_{GE} = 15 V	T_j = 25°C		11,7	13,3	mΩ
		T_j = 125°C		17,3	19	mΩ
$V_{CE(sat)}$	I_{Cnom} = 150 A, V_{GE} = 15 V	T_j = 25°C$_{chiplev.}$		3,4	3,9	V
		T_j = 125°C$_{chiplev.}$		4,5	5	V
C_{ies}	V_{CE} = 25, V_{GE} = 0 V	f = 1 MHz		20		nF
C_{oes}				2		nF
C_{res}				0,55		nF
Q_G	VGE=0V/+20V			2000		nC
$t_{d(on)}$	R_{Gon} = 4 Ω	V_{CC} = 1200V		580		ns
t_r		I_{Cnom}= 150A		100		ns
E_{on}		T_j = 125 °C		95		mJ
$t_{d(off)}$	R_{Goff} = 4 Ω	V_{GE} = ± 15V		750		ns
t_f				40		ns
E_{off}				45		mJ
$R_{th(j-c)}$	per IGBT				0,1	K/W

SKM 200GB173D



SEMITRANS® 3

IGBT Modules

SKM 200GB173D

SKM 200GB173D1

SKM 200GAL173D

SKM 200GAR173D

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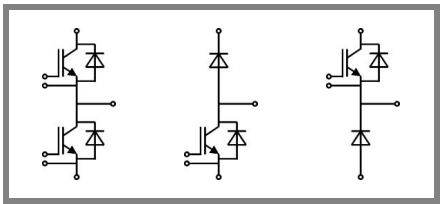


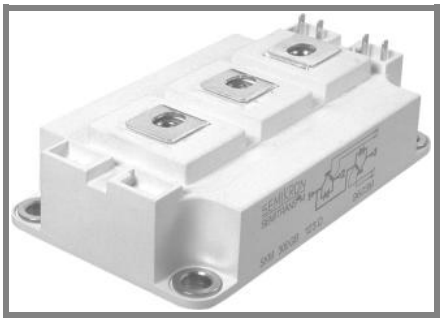
GB GAL GAR

Characteristics						
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Units**
Inverse Diode						
$V_F = V_{EC}$	I_{Fnom} = 150 A; V_{GE} = 0 V	T_j = 25 °$C_{chiplev.}$		2,2	2,7	V
		T_j = 125 °$C_{chiplev.}$		1,9		V
V_{F0}		T_j = 125 °C		1,3	1,5	V
r_F		T_j = 125 °C		4,5	6,2	mΩ
I_{RRM}	I_{Fnom} = 150 A	T_j = 125 °C		85		A
Q_{rr}	di/dt = 1000 A/µs			38		µC
E_{rr}	V_{GE} = -15 V; V_{CC} = 1200 V					mJ
$R_{th(j-c)D}$	per diode				0,32	K/W
FWD						
$V_F = V_{EC}$	I_{Fnom} = 150 A; V_{GE} = 0 V	T_j = 25 °$C_{chiplev.}$		2	2,4	V
		T_j = 125 °$C_{chiplev.}$		1,8		V
V_{F0}		T_j = 125 °C		1,3	1,5	V
r_F		T_j = 125 °C		3,5	4,5	V
I_{RRM}	I_{Fnom} = 150 A	T_j = 125 °C		110		A
Q_{rr}				50		µC
E_{rr}	V_{GE} = -15 V; V_{CC} = 1200 V					mJ
$R_{th(j-c)FD}$	per diode				0,21	K/W
Module						
L_{CE}				15	20	nH
$R_{CC'+EE'}$	res., terminal-chip	T_{case}= 25 °C		0,35		mΩ
		T_{case}= 125 °C		0,5		mΩ
$R_{th(c-s)}$	per module				0,038	K/W
M_s	to heat sink M6		3		5	Nm
w					325	g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.

SKM 200GB173D



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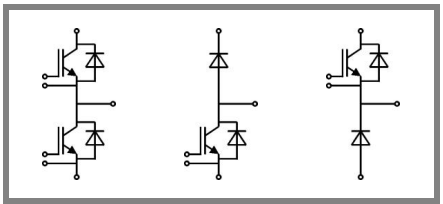


GB **GAL** **GAR**

Z_{th} Symbol	Conditions	Values	Units
$Z_{th(j-c)I}$			
R_i	i = 1	72	mk/W
R_i	i = 2	19	mk/W
R_i	i = 3	6,9	mk/W
R_i	i = 4	2,1	mk/W
tau_i	i = 1	0,0946	s
tau_i	i = 2	0,011	s
tau_i	i = 3	0,0011	s
tau_i	i = 4	0	s
$Z_{th(j-c)D}$			
R_i	i = 1	230	mk/W
R_i	i = 2	70	mk/W
R_i	i = 3	17	mk/W
R_i	i = 4	3	mk/W
tau_i	i = 1	0,0839	s
tau_i	i = 2	0,0069	s
tau_i	i = 3	0,0028	s
tau_i	i = 4	0,0002	s

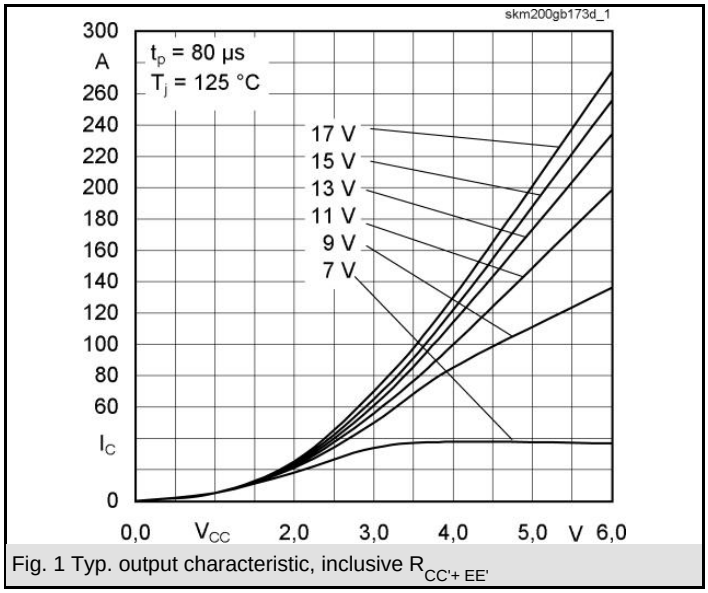


Fig. 1 Typ. output characteristic, inclusive $R_{CC'+EE'}$

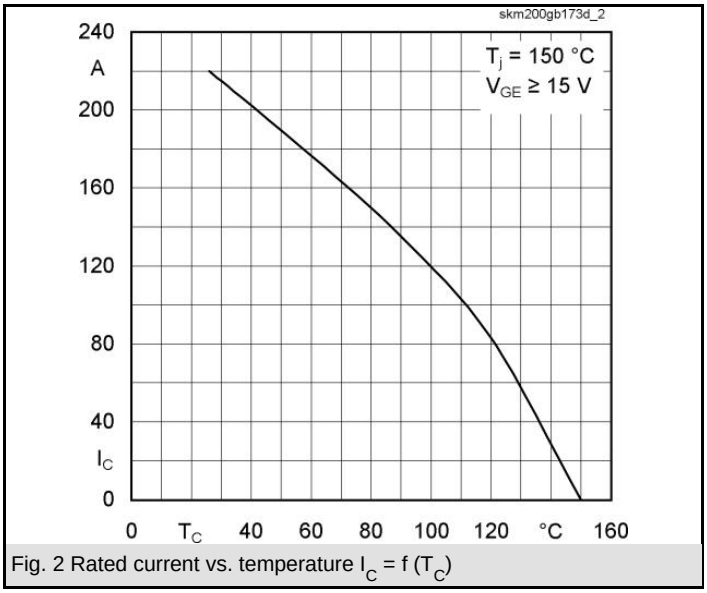


Fig. 2 Rated current vs. temperature $I_C = f(T_C)$

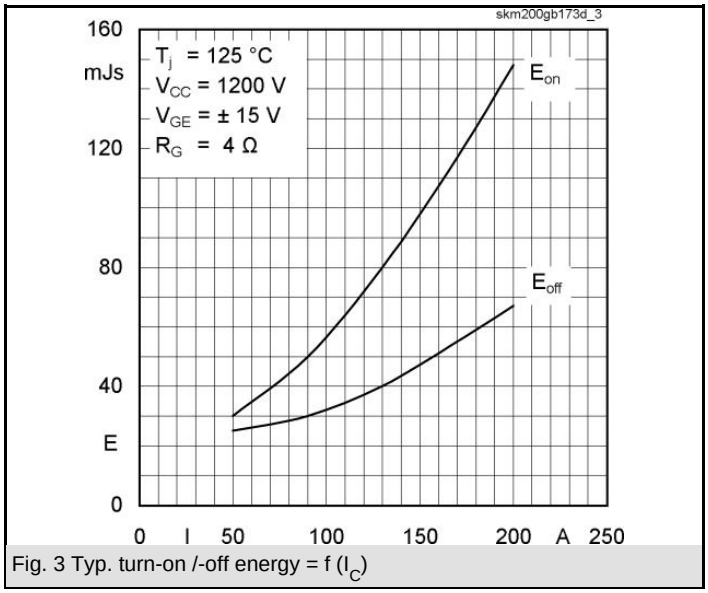


Fig. 3 Typ. turn-on /-off energy = f (I_C)

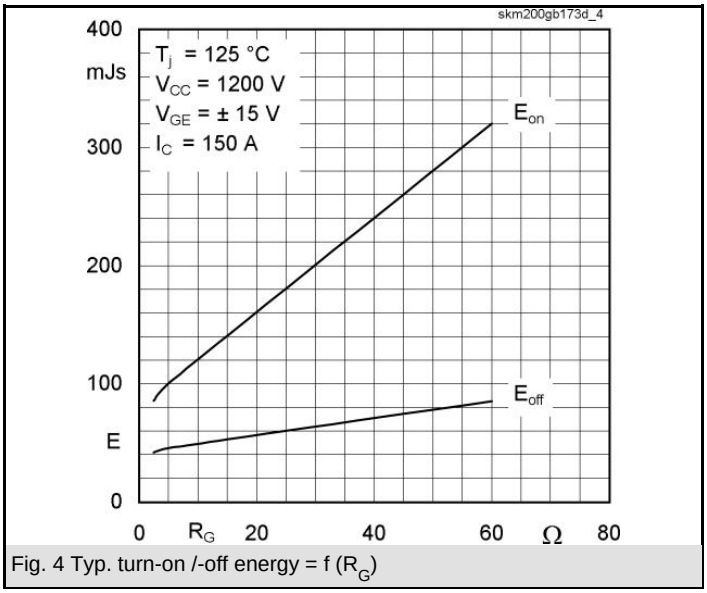


Fig. 4 Typ. turn-on /-off energy = f (R_G)

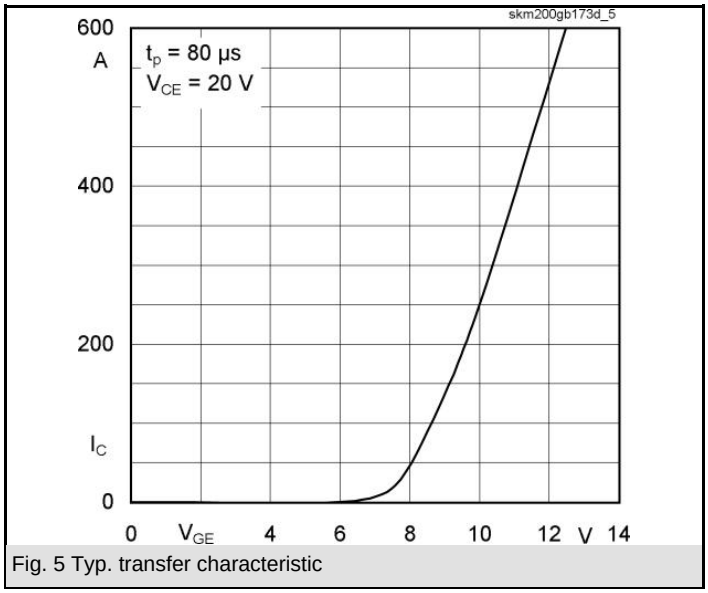


Fig. 5 Typ. transfer characteristic

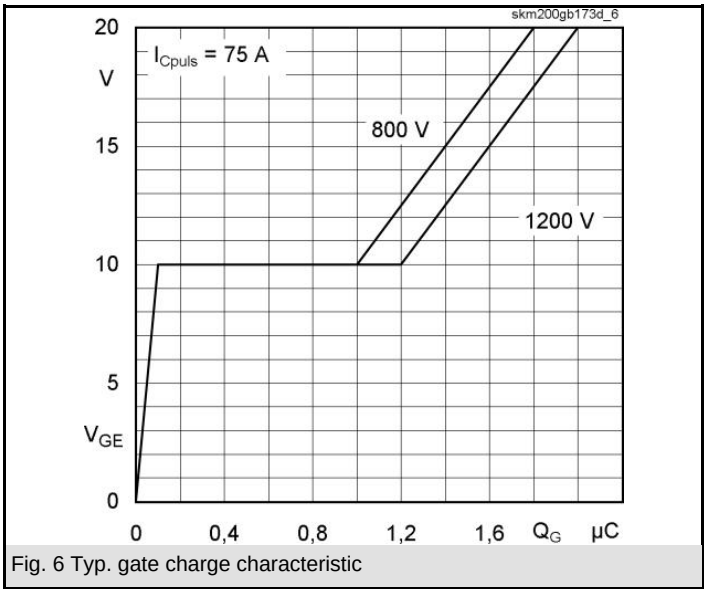


Fig. 6 Typ. gate charge characteristic

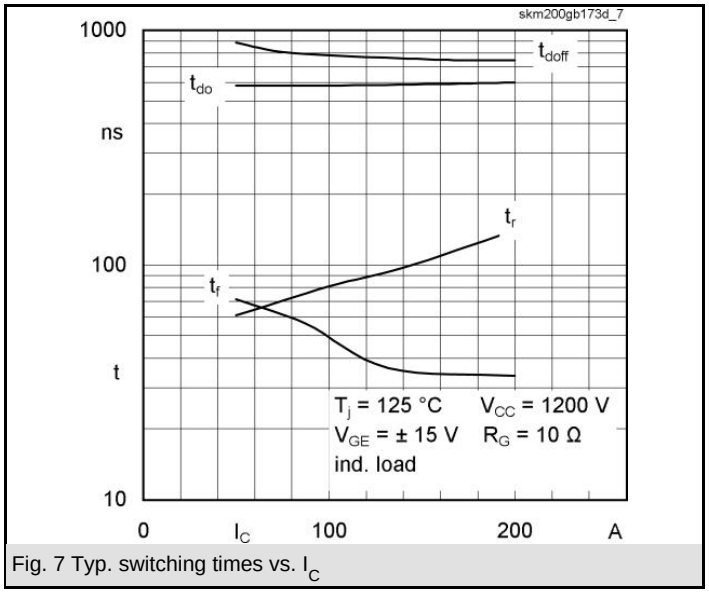


Fig. 7 Typ. switching times vs. I_C

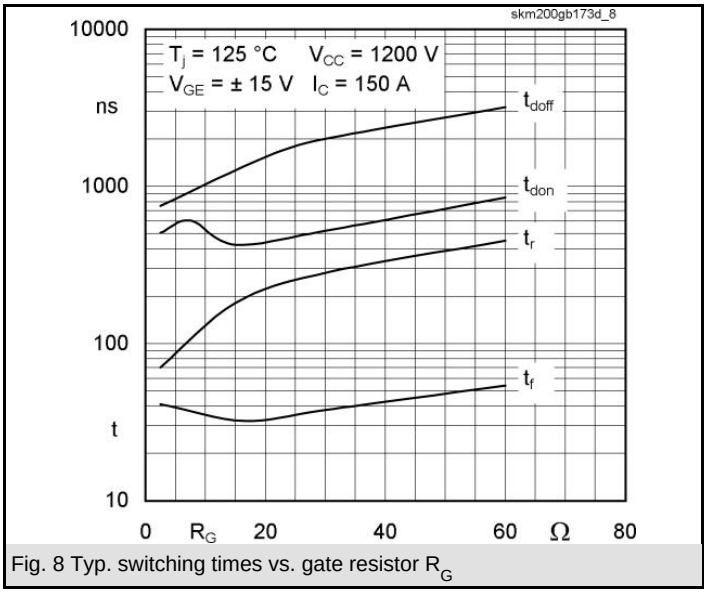


Fig. 8 Typ. switching times vs. gate resistor R_G

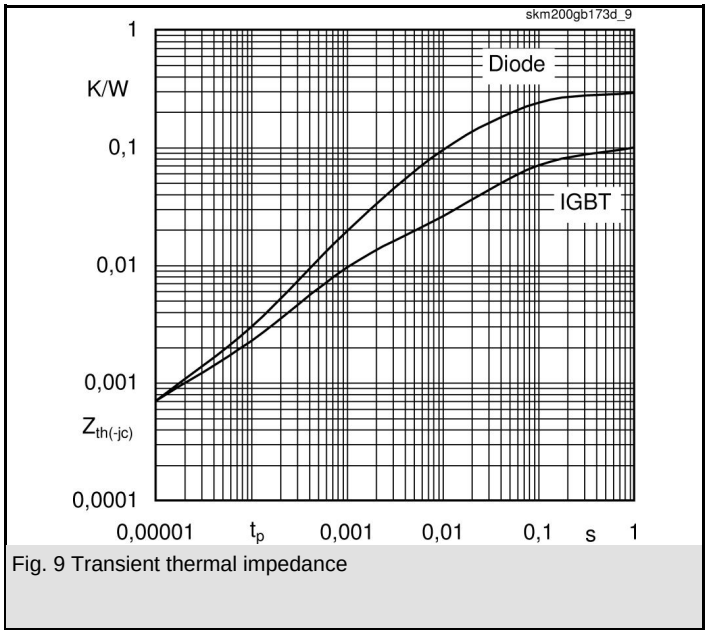


Fig. 9 Transient thermal impedance

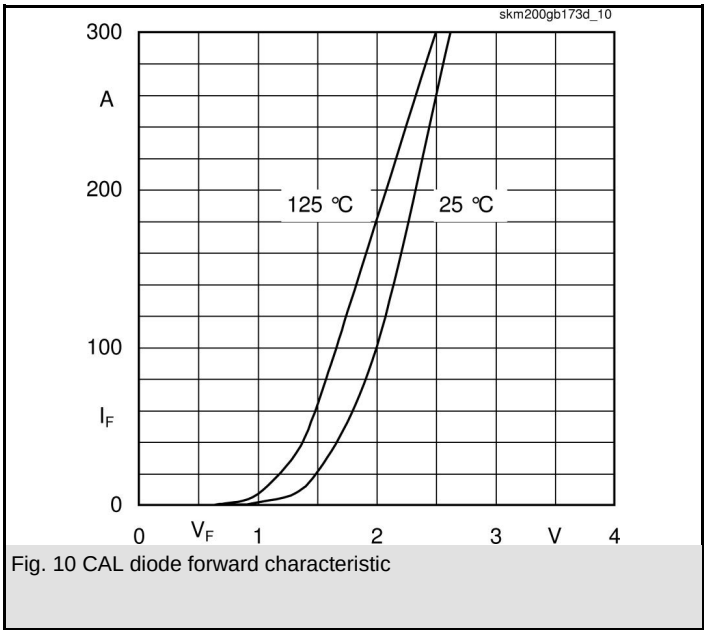


Fig. 10 CAL diode forward characteristic

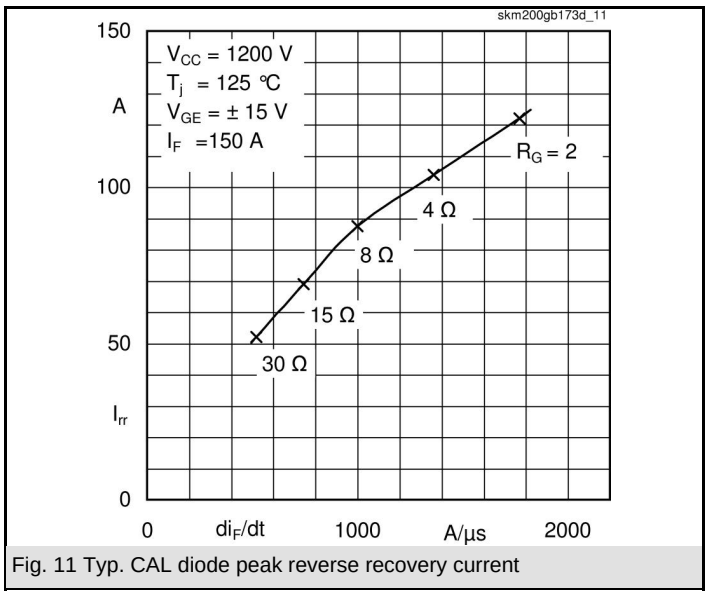


Fig. 11 Typ. CAL diode peak reverse recovery current

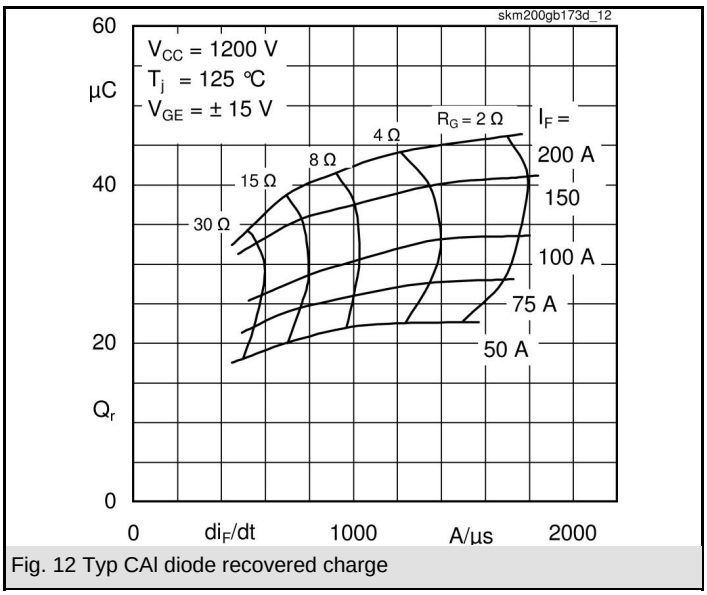
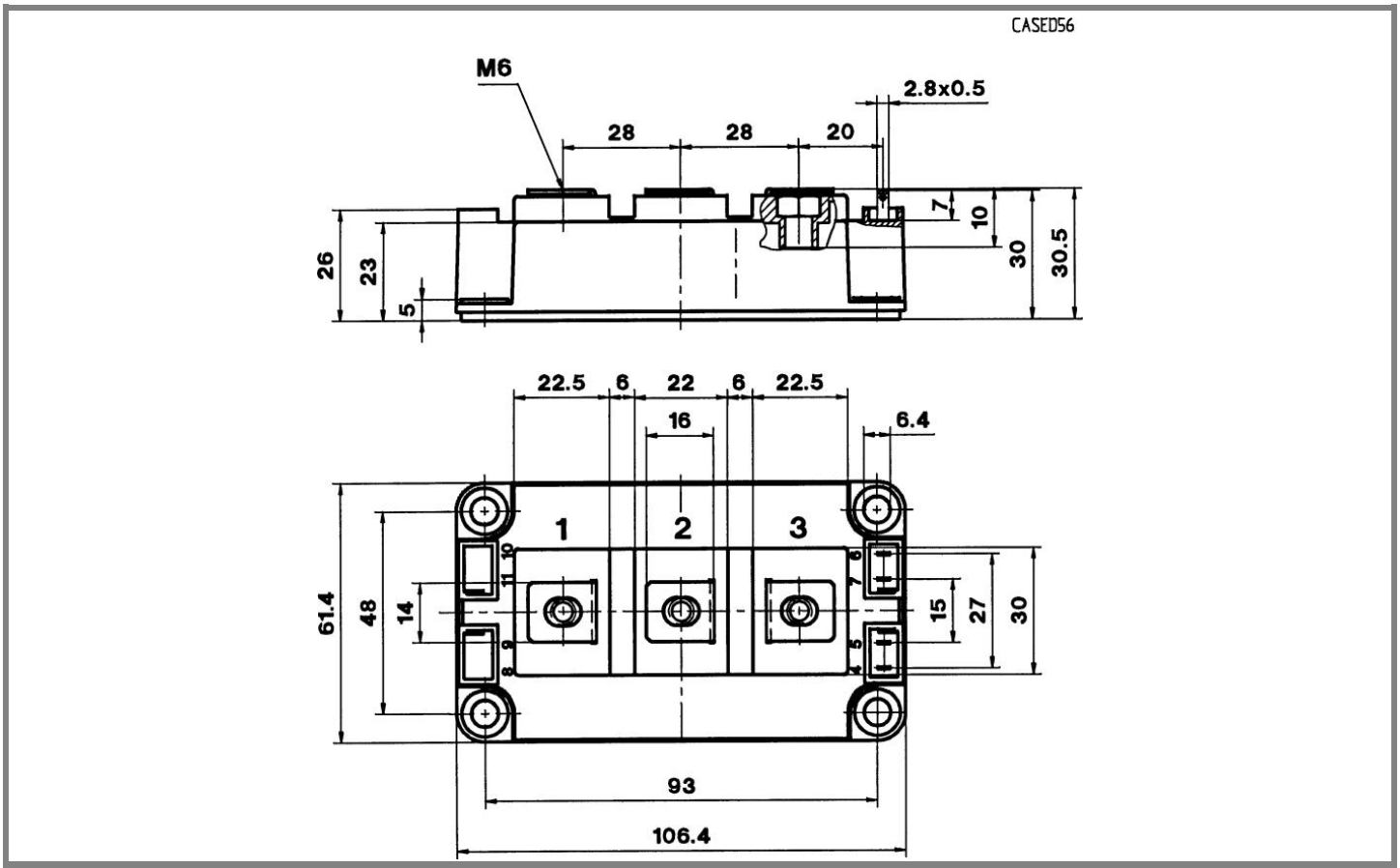
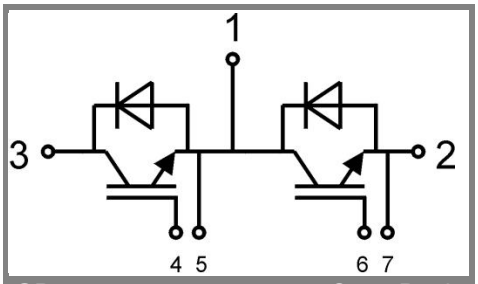


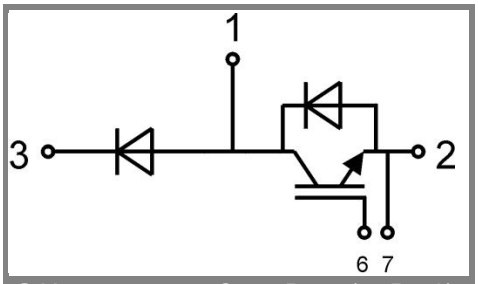
Fig. 12 Typ CAl diode recovered charge



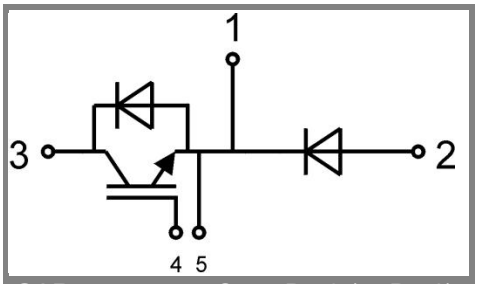
Case D 56



GB Case D 56



GAL Case D 57 (➞ D 56)



GAR Case D 58 (➞ D 56)

